

Title (en)  
Method for packaging and mounting semiconductor device

Title (de)  
Verfahren zur Verpackung und zum Aufbau einer Halbleitervorrichtung

Title (fr)  
Procédé d'emballage et de montage d'un dispositif semiconducteur

Publication  
**EP 1043772 A2 20001011 (EN)**

Application  
**EP 00301898 A 20000308**

Priority  
JP 10259999 A 19990409

Abstract (en)  
A semiconductor device in accordance with the present invention reduces cracks occurring in a junction between a semiconductor device and a mounting substrate due to a heat stress when the semiconductor device is mounted on a printed circuit board or the like. The semiconductor device has a semiconductor element having a thickness of 200  $\mu\text{m}$  or less, an electrode pad formed on the semiconductor element, a post electrically connected to the electrode pad, and a sealing resin for sealing a surface where circuitry is formed and the post. Furthermore, a manufacturing method for a semiconductor device in accordance with the present invention includes a step for forming an electrode pad on a main surface of a semiconductor wafer, a step for forming a post to be connected to the electrode pad, a step for resin-sealing the main surface of the semiconductor wafer and the post, a step for forming a groove from a surface of the resin to a predetermined depth of the semiconductor wafer, and a step for polishing a rear surface of the semiconductor wafer to a bottom of the groove and dividing the semiconductor wafer into individual semiconductor devices. <IMAGE> <IMAGE> <IMAGE> <IMAGE> <IMAGE>

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IPC 8 full level  
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